

# Dmitry Yurasov

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

50  
papers

206  
citations

8  
h-index

12  
g-index

53  
ext. papers

237  
ext. citations

1  
avg, IF

2.54  
L-index

#	Paper	IF	Citations
50	Influence of irradiation by Swift Heavy Ions (SHI) on electronic magnetotransport in Sb layer in silicon. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2022</b> , 138, 115047	3	0
49	Formation and Optical Properties of Locally Strained Ge Microstructures Embedded into Cavities. <i>Semiconductors</i> , <b>2021</b> , 55, 531	0.7	
48	Spin pump induced inverse spin Hall effect observed in Bi-doped n-type Si. <i>Physical Review B</i> , <b>2020</b> , 101,	3.3	2
47	Influence of the Growth Conditions and Doping Level on the Luminescence Kinetics of Ge:Sb Layers Grown on Silicon. <i>Semiconductors</i> , <b>2020</b> , 54, 811-816	0.7	0
46	Effect of antimony doping on the energy of optical transitions in n-Ge layers grown on Si (001) and Ge (001) substrates. <i>Journal of Applied Physics</i> , <b>2020</b> , 127, 165701	2.5	0
45	Enhancement of the Luminescence Signal from Self-Assembled Ge(Si) Nanoislands due to Interaction with the Modes of Two-Dimensional Photonic Crystals. <i>Semiconductors</i> , <b>2020</b> , 54, 975-981	0.7	0
44	Comparative Analysis of the Luminescence of Ge:Sb Layers Grown on Ge(001) and Si(001) Substrates. <i>Semiconductors</i> , <b>2019</b> , 53, 1318-1323	0.7	1
43	Locally Strained Ge/SOI Structures with an Improved Heat Sink as an Active Medium for Silicon Optoelectronics. <i>Semiconductors</i> , <b>2019</b> , 53, 1324-1328	0.7	1
42	Influence of Annealing on the Properties of Ge:Sb/Si(001) Layers with an Antimony Concentration Above Its Equilibrium Solubility in Germanium. <i>Semiconductors</i> , <b>2019</b> , 53, 882-886	0.7	3
41	Light emission from Ge(Si)/SOI self-assembled nanoislands embedded in photonic crystal slabs of various periods with and without cavities. <i>Semiconductor Science and Technology</i> , <b>2019</b> , 34, 024003	1.8	12
40	On the Application of Strain-Compensating GaAsP Layers for the Growth of InGaAs/GaAs Quantum-Well Laser Heterostructures Emitting at Wavelengths above 1100 nm on Artificial Ge/Si Substrates. <i>Semiconductors</i> , <b>2018</b> , 52, 1547-1550	0.7	3
39	Influence of thermal annealing on the electrical and luminescent properties of heavily Sb-doped Ge/Si(001) layers. <i>Semiconductor Science and Technology</i> , <b>2018</b> , 33, 124019	1.8	6
38	A New Limitation of the Depth Resolution in TOF-SIMS Elemental Profiling: the Influence of a Probing Ion Beam. <i>Technical Physics Letters</i> , <b>2018</b> , 44, 320-323	0.7	1
37	Stimulated Emission in the 1.3-1.5 $\mu\text{m}$ Spectral Range from AlGaInAs Quantum Wells in Hybrid Light-Emitting III-V Heterostructures on Silicon Substrates. <i>Semiconductors</i> , <b>2018</b> , 52, 1495-1499	0.7	
36	Formation and Properties of Locally Tensile Strained Ge Microstructures for Silicon Photonics. <i>Semiconductors</i> , <b>2018</b> , 52, 1442-1447	0.7	2
35	Stimulated Emission at 1.3- $\mu\text{m}$ Wavelength in Metamorphic InGaAs/InGaAsP Structure with Quantum Wells Grown on Ge/Si(001) Substrate. <i>Technical Physics Letters</i> , <b>2018</b> , 44, 735-738	0.7	
34	On the stimulated emission of InGaAs/GaAs/AlGaAs laser structures grown by MOCVD on exact and inclined Ge/Si(001) substrates. <i>Semiconductors</i> , <b>2017</b> , 51, 663-666	0.7	5

33	Selective etching of Si, SiGe, Ge and its usage for increasing the efficiency of silicon solar cells. <i>Semiconductors</i> , <b>2017</b> , 51, 1542-1546	0.7	7
32	Antimony segregation in Si layers grown by molecular beam epitaxy on Si wafers with different crystallographic orientations. <i>Semiconductors</i> , <b>2017</b> , 51, 1552-1556	0.7	
31	Technology of the production of laser diodes based on GaAs/InGaAs/AlGaAs structures grown on a Ge/Si substrate. <i>Semiconductors</i> , <b>2017</b> , 51, 1477-1480	0.7	4
30	Electroluminescence of structures with self-assembled Ge(Si) nanoislands confined between strained Si layers. <i>Semiconductors</i> , <b>2016</b> , 50, 1657-1661	0.7	
29	On the radiative recombination and tunneling of charge carriers in SiGe/Si heterostructures with double quantum wells. <i>Semiconductors</i> , <b>2016</b> , 50, 1604-1608	0.7	
28	Influence of surface roughness on a change in the growth mode from two-dimensional to three-dimensional for strained SiGe heterostructures. <i>Semiconductors</i> , <b>2016</b> , 50, 1630-1634	0.7	1
27	Nonlinear calibration curves in secondary ion mass spectrometry for quantitative analysis of gesi heterostructures with nanoclusters. <i>Technical Physics Letters</i> , <b>2016</b> , 42, 243-247	0.7	2
26	Plastic relaxation in GeSi layers on Si (001) and Si (115) substrates. <i>Semiconductors</i> , <b>2015</b> , 49, 19-22	0.7	
25	Hodographs in diode-structure diagnostics. <i>Semiconductors</i> , <b>2015</b> , 49, 1443-1447	0.7	
24	Impact of growth and annealing conditions on the parameters of Ge/Si(001) relaxed layers grown by molecular beam epitaxy. <i>Semiconductors</i> , <b>2015</b> , 49, 1415-1420	0.7	18
23	The waveguide effect of InGaAs quantum wells in a GaAs structure on Si substrate with Ge buffer layer. <i>Technical Physics Letters</i> , <b>2015</b> , 41, 648-650	0.7	2
22	Growth of light-emitting SiGe heterostructures on strained silicon-on-insulator substrates with a thin oxide layer. <i>Semiconductors</i> , <b>2015</b> , 49, 1104-1110	0.7	3
21	Antimony segregation in Ge and formation of n-type selectively doped Ge films in molecular beam epitaxy. <i>Journal of Applied Physics</i> , <b>2015</b> , 118, 145701	2.5	19
20	Quantitative calibration and germanium SIMS depth profiling in Ge x Si1-x/Si heterostructures. <i>Semiconductors</i> , <b>2014</b> , 48, 1109-1117	0.7	5
19	A new approach to the diagnostics of nanoislands in Ge x Si1-x/Si heterostructures by secondary ion mass spectrometry. <i>Technical Physics Letters</i> , <b>2014</b> , 40, 601-605	0.7	7
18	Use of related parameters in X-ray diffraction analysis of multilayer structures with allowance for the layer growth time. <i>Technical Physics</i> , <b>2014</b> , 59, 402-406	0.5	3
17	Recovery of SIMS depth profiles with account for nonstationary effects. <i>Applied Surface Science</i> , <b>2014</b> , 307, 33-41	6.7	13
16	Transition from the two- to three-dimensional growth of Ge films upon deposition onto relaxed SiGe/Si(001) buffer layers. <i>Semiconductors</i> , <b>2013</b> , 47, 427-432	0.7	3

15	Antimony segregation in stressed SiGe heterostructures grown by molecular beam epitaxy. <i>Semiconductors</i> , <b>2013</b> , 47, 1481-1484	0.7	1
14	New approach to the X-ray diffraction analysis of test structures during flow calibration in epitaxial growth reactors. <i>Journal of Surface Investigation</i> , <b>2012</b> , 6, 494-497	0.5	2
13	Layer-by-layer analysis of structures containing $\delta$ layers by secondary ion mass spectrometry taking into account the TOF-SIMS-5 depth resolution function. <i>Journal of Surface Investigation</i> , <b>2012</b> , 6, 574-577	0.5	2
12	Barrier-height modification in Schottky silicon diodes with highly doped 3D and 2D layers. <i>Semiconductors</i> , <b>2012</b> , 46, 1358-1361	0.7	6
11	Optical monitoring of technological parameters during molecular-beam epitaxy. <i>Semiconductors</i> , <b>2012</b> , 46, 1471-1475	0.7	18
10	Method for taking into account the shift parameter in the deconvolution of the depth composition distribution of semiconductor structures from SIMS depth profiles. <i>Semiconductors</i> , <b>2012</b> , 46, 1481-1486	0.7	5
9	Transition from planar to island growth mode in SiGe structures fabricated on SiGe/Si(001) strain-relaxed buffers. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 151601	3.4	5
8	Method of selective doping of silicon by segregating impurities. <i>Technical Physics Letters</i> , <b>2011</b> , 37, 824-826		1
7	TOF-SIMS 5 instrument sensitivity to matrix elements in GeSi Layers: Analysis based on recording of complex secondary ions. <i>Journal of Surface Investigation</i> , <b>2011</b> , 5, 591-594	0.5	9
6	Direct comparison of superlattice periods measured with X-ray diffractometry and optical interferometry. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , <b>2011</b> , 75, 40-43	0.4	2
5	Secondary cluster ions Ge $\delta$ and Ge $\beta$ for improving depth resolution of SIMS depth profiling of GeSi/Si heterostructures. <i>Semiconductors</i> , <b>2010</b> , 44, 401-404	0.7	9
4	Study of the transition of the epitaxial Ge film from layer-to-layer to three-dimensional growth in heterostructures with strained SiGe sublayers. <i>Semiconductors</i> , <b>2010</b> , 44, 519-524	0.7	2
3	Influence of elastic strains in sublayers on the critical thickness of the Stranski-Krastanov transition for the GeSi/Si(001) system. <i>Journal of Surface Investigation</i> , <b>2009</b> , 3, 548-553	0.5	6
2	Critical thickness for the Stranski-Krastanov transition treated with the effect of segregation. <i>Semiconductors</i> , <b>2008</b> , 42, 563-570	0.7	15
1	Comparison of III-V Heterostructures Grown on Ge/Si, Ge/SOI, and GaAs. <i>Semiconductors</i> , 1	0.7	